

74V1G79

SINGLE POSITIVE EDGE TRIGGERED D-TYPE FLIP-FLOP

■ HIGH SPEED:

 $f_{MAX} = 180MHz$ (TYP.) at $V_{CC} = 5V$

■ LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25$ °C

■ HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)

- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL} = 8\text{mA (MIN)}$ at $V_{CC} = 4.5\text{V}$
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V_{CC}(OPR) = 2V to 5.5V
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

PACKAGE	T&R
SOT23-5L	74V1G79STR
SOT323-5L	74V1G79CTR

DESCRIPTION

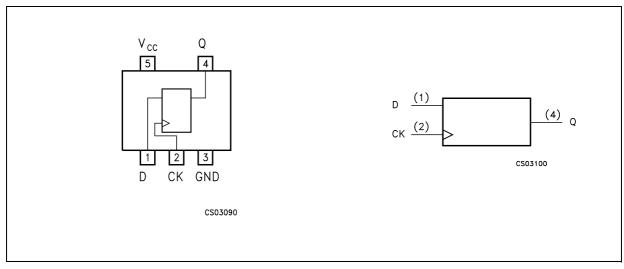
The 74V1G79 is an advanced high-speed CMOS SINGLE POSITIVE EDGE TRIGGERED D-TYPE FLIP-FLOP fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. it is designed to operate from 2V to 5.5V, making this device ideal for portable applications.

This D-Type flip-flop is controlled by a clock input (CK). On the positive transition of the clock, the Q output will be set to the logic state that was setup at the D input.

Following the hold time interval, data at the D input can be changed without affecting the level at the output. Power down protection is provided on inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V systems.

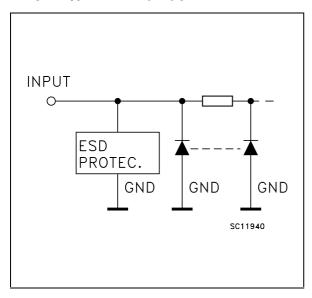
It's available in the commercial and extended temperature range. All inputs and output are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/10

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION				
1	D	Data Input				
2	СК	Clock Input (Positive Edge)				
4	Q	Flip-Flop Output				
3	GND	Ground (0V)				
5	V _{CC}	Positive Supply Voltage				

TRUTH TABLE

D	СК	Q
L		L
Н		Н
L		Qn
Н	_	Qn

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V_{CC} = 3.3 \pm 0.3V) (V_{CC} = 5.0 \pm 0.5V)	0 to 100 0 to 20	ns/V ns/V

¹⁾ V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

		Т	est Condition		Value						
Symbol	Parameter	V _{CC}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		V
V _{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	V
V _{OH}	High Level Output	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		
Voltage	3.0	I _O =-50 μA	2.9	3.0		2.9		2.9			
		4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
		3.0	I _O =-4 mA	2.58			2.48		2.4		
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3 \text{ns}$)

		7	est Co	ondition				Value				
Symbol Pa	Parameter	v _{cc}	CL		Т	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay	3.3 ^(*)	15			5.4	8.0	1.0	9.5	1.0	10.5	
	Time CK to Q	3.3 ^(*)	50			5.9	8.5	1.0	10.0	1.0	11.0	ns
		5.0 ^(**)	15			3.9	5.5	1.0	6.5	1.0	7.5	115
		5.0 ^(**)	50			4.5	6.5	1.0	7.5	1.0	8.5	
t _W	CK Pulse Width,	3.3 ^(*)					4.0		4.0		4.0	no
	HIGH or LOW	5.0 ^(**)					3.0		3.0		3.0	ns
t _s	Setup Time D to	3.3 ^(*)					4.0		4.0		4.0	
	CK, HIGH or LOW	5.0 ^(**)					3.0		3.0		3.0	ns
t _h	Hold Time D to CK,	3.3 ^(*)					1.0		1.0		1.0	
	HIGH or LOW	5.0 ^(**)					1.0		1.0		1.0	ns
f _{MAX}	Maximum Clock	3.3 ^(*)	50		100	120		90		90		MHz
	Frequency	5.0 ^(**)	50		165	180		150		150		IVITZ

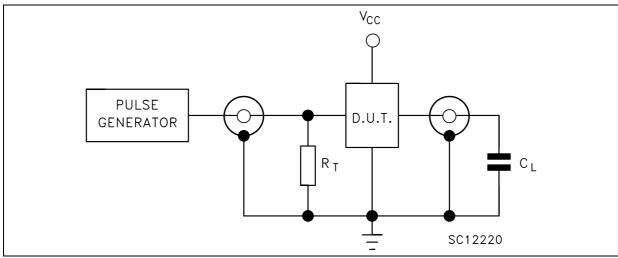
^(*) Voltage range is 3.3V ± 0.3V (**) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

		Test Condition		Value						
Symbol	Parameter		T _A = 25°C -40 to 85°C -55 to 12		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)			8						pF

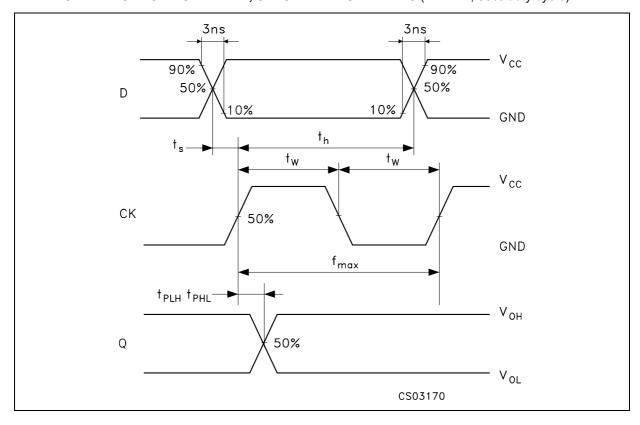
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} x V_{CC} x f_{IN} + I_{CC}

TEST CIRCUIT



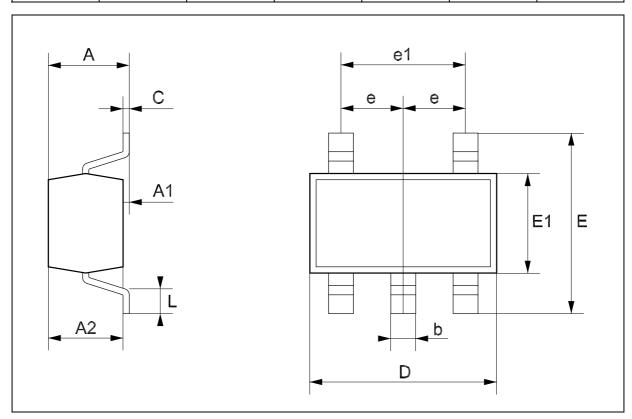
 C_L = 15/50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAY, SETUP AND HOLD TIMES (f=1MHz; 50% duty cycle)



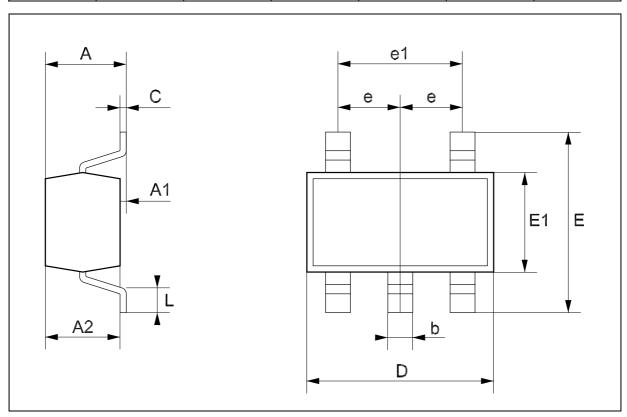
SOT23-5L MECHANICAL DATA

DIM		mm.		mils			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.15	0.0		5.9	
A2	0.90		1.30	35.4		51.2	
b	0.35		0.50	13.7		19.7	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	2.60		3.00	102.3		118.1	
E1	1.50		1.75	59.0		68.8	
е		0.95			37.4		
e1		1.9			74.8		
L	0.35		0.55	13.7		21.6	



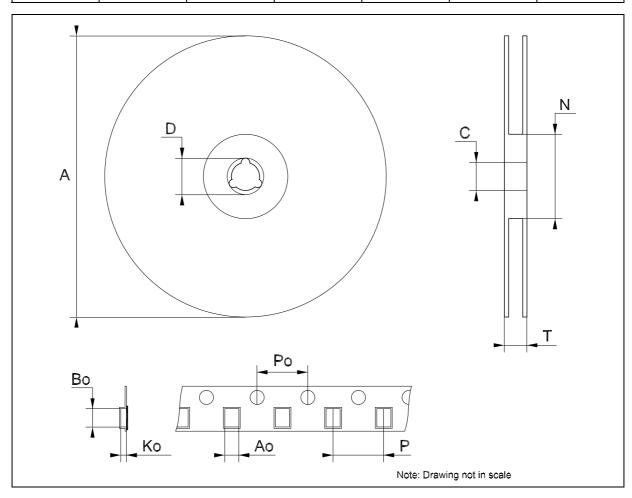
SOT323-5L MECHANICAL DATA

DIM		mm.		mils			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А	0.80		1.10	31.5		43.3	
A1	0.00		0.10	0.0		3.9	
A2	0.80		1.00	31.5		39.4	
b	0.15		0.30	5.9		11.8	
С	0.10		0.18	3.9		7.1	
D	1.80		2.20	70.9		86.6	
E	1.80		2.40	70.9		94.5	
E1	1.15		1.35	45.3		53.1	
е		0.65			25.6		
e1		1.3			51.2		
L	0.10		0.30	3.9		11.8	



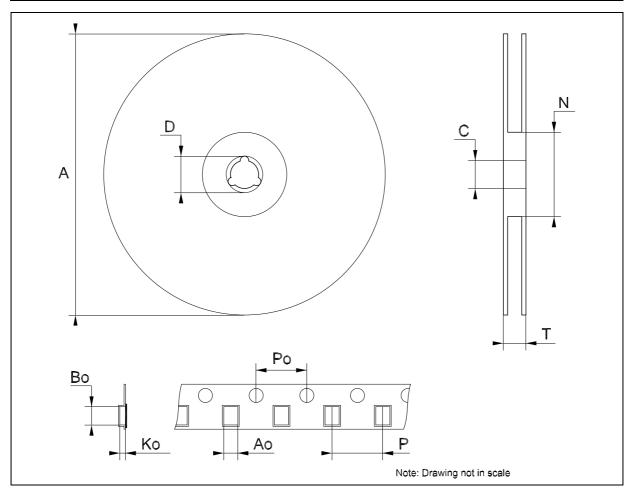
Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α			180			7.086	
С	12.8	13.0	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	60			2.362			
Т			14.4			0.567	
Ao	3.13	3.23	3.33	0.123	0.127	0.131	
Во	3.07	3.17	3.27	0.120	0.124	0.128	
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58	
Ро	3.9	4.0	4.1	0.153	0.157	0.161	
Р	3.9	4.0	4.1	0.153	0.157	0.161	



Tape & Reel SOT323-xL MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	175	180	185	6.889	7.086	7.283	
С	12.8	13	13.2	0.504	0.512	0.519	
D	20.2			0.795			
N	59.5	60	60.5		2.362		
Т			14.4			0.567	
Ao		2.25			0.088		
Во		2.7			0.106		
Ko		1.2			0.047		
Po	3.98	4	4.2	0.156	0.157	0.165	
Р	3.98	4	4.2	0.156	0.157	0.165	



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